ABSTRACT

Disclosed are a substrate carrying device (20) and a plasma processing equipment. An upper surface of the substrate carrying device (20) is provided with a plurality of substrate mounting locations (201), and heat-exchange gas inlet passages (23, 24, 25) are arranged in the substrate carrying device (20) corresponding to each substrate mounting location (201), so as to guide a heat exchange gas to the upper surface of the substrate mounting location (201). The heat-exchange gas inlet passages comprise peripheral inlet passages and a middle inlet passage, wherein gas inlets (23, 24, 25) of the peripheral inlet passages and the middle inlet passage are all in communication with an external gas source; gas outlets of the peripheral inlet passages are arranged in the peripheral region of the upper surface of the substrate mounting location (201); and a gas outlet of the middle inlet passage is arranged in the middle region of the upper surface of the substrate mounting location (201). The substrate carrying device (20) and the plasma processing equipment can improve the heat exchange effect of the peripheral region of a processed workpiece (21), so that the temperature of the peripheral region and the middle region of the processed workpiece (21) can be enabled to tend to be uniform, and then the uniformity of the plasma processing technology can be improved.